

FEB 12 2008Serial No. 10/574,556
Filing Date: April 3, 2006Customer No. 26,289
Attorney's Docket No. 2003JP322**Complete set of claims**

1(cancelled).

2(cancelled).

3(cancelled).

4(cancelled).

5(currently amended). A process for producing a semiconductor device, comprising the steps of: forming an insulating layer and an etching stopper layer on a substrate; removing part of the insulating layer by dry etching; and filling an electrically conductive material into a groove or hole thus formed, wherein said etching stopper layer is formed by curing a composition comprising a silicon-containing polymer, wherein 5% to 100% by mole, based on the total number of moles of silicon contained in the silicon-containing polymer, of silicon is contained in a disilylbenzene structure, further where the silicon-containing polymer has a carbon content of not less than 30% by weight, and further where the etching stopper layer is cured at a temperature in the range of 200°C to 500°C for 30 to 50 minutes.

6(cancelled).

7(cancelled).

8(cancelled).

9(cancelled).

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10(cancelled).

11(cancelled).

12(cancelled).

13(cancelled).

14(cancelled).

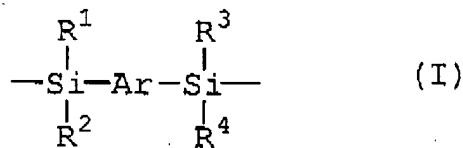
15(cancelled).

16(cancelled).

17(cancelled).

18(cancelled).

19(previously presented). The process of claim 5, where the disilylbenzene structure is represented by formula (I),

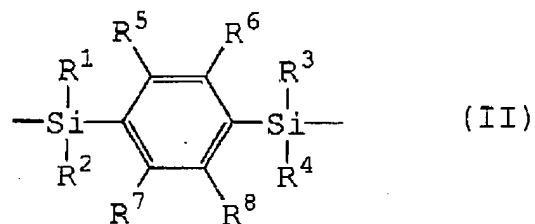


wherein R¹ to R⁴ each independently are selected from hydrogen, an alkyl group, an alkenyl group, a cycloalkyl group, an aryl group, an aralkyl group, an alkylamino group, and an alkylsilyl group, and Ar represents an aryl group.

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20(previously presented). The process of claim 5, where the disilylbenzene structure is represented by formula (II),



wherein R¹ to R⁴ each independently are selected from hydrogen, an alkyl group, an alkenyl group, a cycloalkyl group, an aryl group, an aralkyl group, an alkylamino group, and an alkylsilyl group; and R⁵ to R⁸ are independently selected from hydrogen, a C₁ to C₃ alkyl group, a halogen atom, a C₁ to C₃ alkoxide group, and a C₁ to C₃ amino group.